

09/848, 718

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<u>L1</u>	(field adj effect adj transistor) or fet	63621	<u>L1</u>

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L4: Entry 1 of 7

File: USPT

Aug 27, 2002

US-PAT-NO: 6441418

DOCUMENT-IDENTIFIER: US 6441418 B1

TITLE: Spacer narrowed, dual width contact for charge gain reduction

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC
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☐ 2. Document ID: US 6429477 B1

L4: Entry 2 of 7

File: USPT

Aug 6, 2002

US-PAT-NO: 6429477

DOCUMENT-IDENTIFIER: US 6429477 B1

TITLE: Shared body and diffusion contact structure and method for fabricating same

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC
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☐ 3. Document ID: US 6380039 B2

L4: Entry 3 of 7

File: USPT

Apr 30, 2002

US-PAT-NO: 6380039

DOCUMENT-IDENTIFIER: US 6380039 B2

TITLE: Method for forming a FET having L-shaped insulating spacers

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KWIC
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☐ 4. Document ID: US 6313003 B1

L4: Entry 4 of 7

File: USPT

Nov 6, 2001

US-PAT-NO: 6313003  
DOCUMENT-IDENTIFIER: US 6313003 B1

TITLE: Fabrication process for metal-insulator-metal capacitor with low gate resistance

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KWIC
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☐ 5. Document ID: US 6174794 B1

L4: Entry 5 of 7                      File: USPT                      Jan 16, 2001

US-PAT-NO: 6174794  
DOCUMENT-IDENTIFIER: US 6174794 B1

TITLE: Method of making high performance MOSFET with polished gate and source/drain feature

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KWIC
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☐ 6. Document ID: US 4811078 A

L4: Entry 6 of 7                      File: USPT                      Mar 7, 1989

US-PAT-NO: 4811078  
DOCUMENT-IDENTIFIER: US 4811078 A

TITLE: Integrated circuit device and process with tin capacitors

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KWIC
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☐ 7. Document ID: US 4811076 A

L4: Entry 7 of 7                      File: USPT                      Mar 7, 1989

US-PAT-NO: 4811076  
DOCUMENT-IDENTIFIER: US 4811076 A

TITLE: Device and process with doubled capacitors

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KWIC
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